



Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	500	
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.52
Q _g (Max.) (nC)	52	
Q _{gs} (nC)	13	
Q _{gd} (nC)	18	
Configuration	Single	

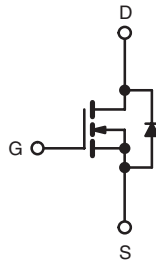
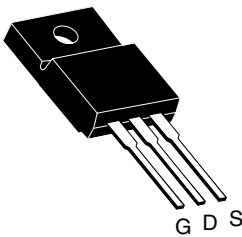
FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} Specified
- Compliant to RoHS directive 2002/95/EC



RoHS* COMPLIANT

TO-220 FULLPAK



N-Channel MOSFET

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- High Voltage Isolation = 2.5 kV_{RMS} (t = 60 s, f = 60 Hz)

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half and Full Bridge Convertors
- Power Factor Correction Boost

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFIB7N50APbF
	SiHFIB7N50A-E3
SnPb	IRFIB7N50A
	SiHFIB7N50A


ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	500	V
Gate-Source Voltage			V _{GS}	± 30	
Continuous Drain Current ^f	V _{GS} at 10 V	T _C = 25 °C	I _D	6.6	A
Continuous Drain Current		T _C = 100 °C		4.2	
Pulsed Drain Current ^{a, e}			I _{DM}	44	
Linear Derating Factor				0.48	W/°C
Single Pulse Avalanche Energy ^{b, e}			E _{AS}	275	mJ
Repetitive Avalanche Current ^{a, e}			I _{AR}	11	A
Repetitive Avalanche Energy ^a			E _{AR}	6.0	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	60	W
Peak Diode Recovery dV/dt ^{c, e}			dV/dt	6.9	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 ^d	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting T_J = 25 °C, L = 4.5 mH, R_G = 25 Ω, I_{AS} = 11 A (see fig. 12).
- I_{SD} ≤ 11 A, di/dt ≤ 140 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.
- Uses IRFB11N50A, SiHFB11N50A data and test conditions.
- Drain current limited by maximum junction temperature.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	2.1	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}^d$	-	610	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}^b$	-	-	0.52	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 6.6\text{ A}^d$	6.1	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 ^d	-	1423	-	μF
Output Capacitance	C_{oss}		-	208	-	
Reverse Transfer Capacitance	C_{rss}		-	8.1	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	2000	-
			$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	55	-
Effective Output Capacitance	$C_{oss\text{ eff.}}$			-	97	-
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^{b, d}	-	-	52	nC
Gate-Source Charge	Q_{gs}		-	-	13	
Gate-Drain Charge	Q_{gd}		-	-	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 11\text{ A}, R_G = 9.1\text{ }\Omega, R_D = 22\text{ }\Omega$, see fig. 10 ^{b, d}	-	14	-	ns
Rise Time	t_r		-	35	-	
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	
Fall Time	t_f		-	28	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	6.6	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	44	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 11\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b, d$	-	510	770	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.4	5.1	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
- d. Uses IRFB11N50A, SiHF11N50A data and test conditions.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

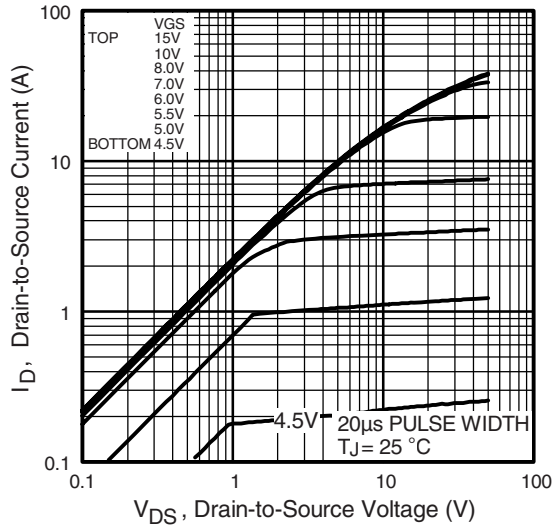


Fig. 1 - Typical Output Characteristics

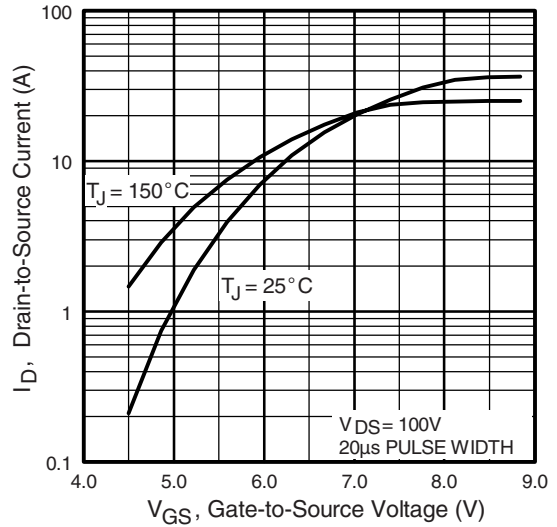


Fig. 3 - Typical Transfer Characteristics

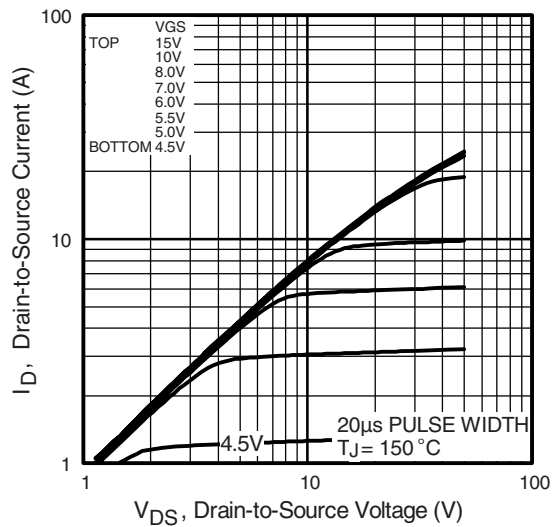


Fig. 2 - Typical Output Characteristics

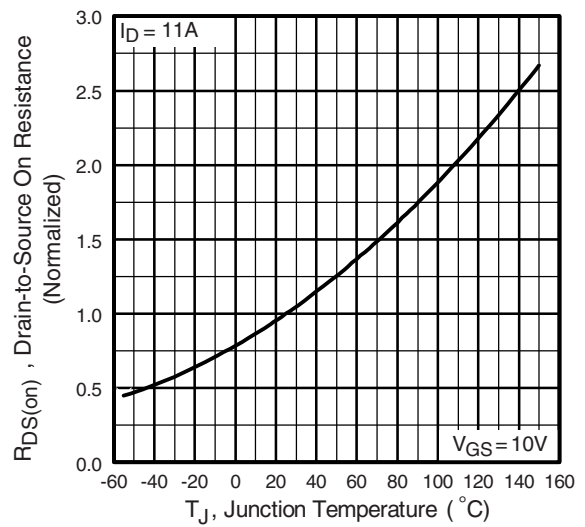


Fig. 4 - Normalized On-Resistance vs. Temperature

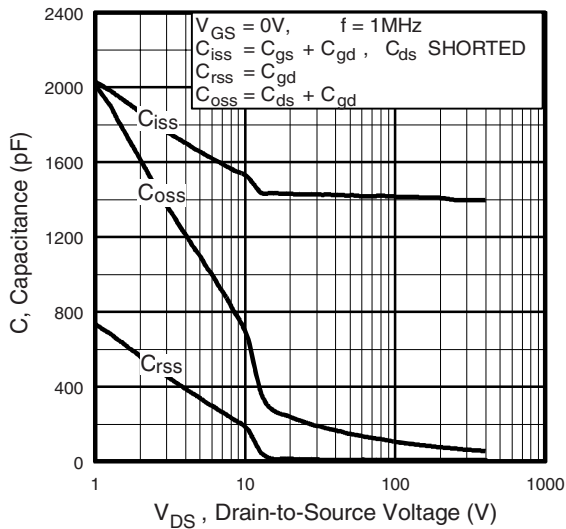


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

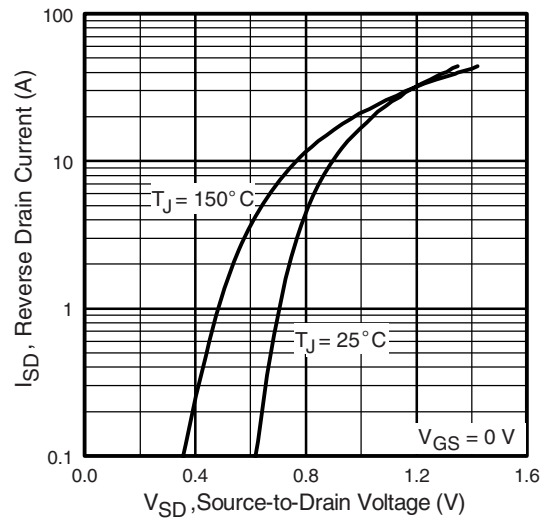


Fig. 7 - Typical Source-Drain Diode Forward Voltage

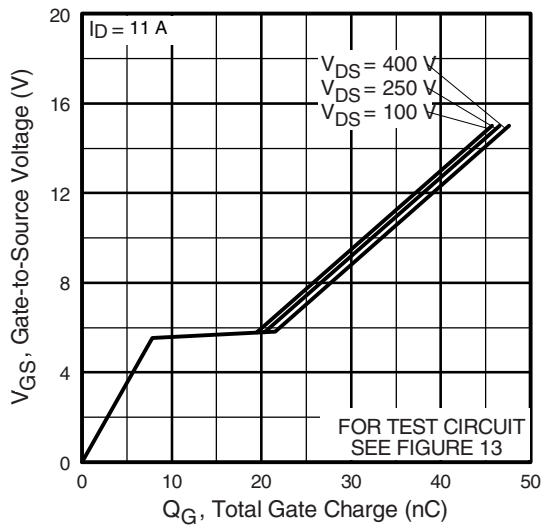


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

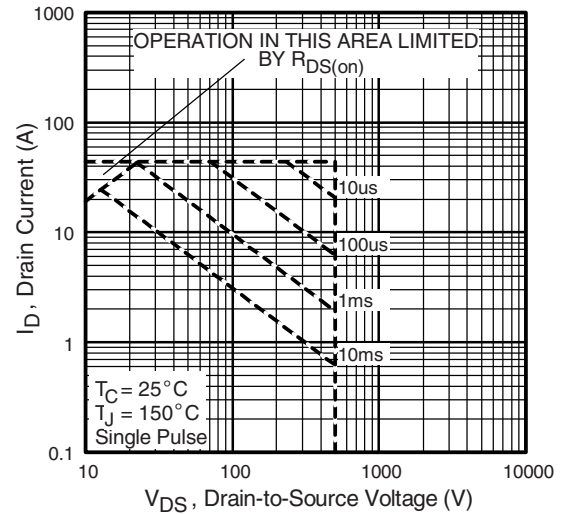


Fig. 8 - Maximum Safe Operating Area

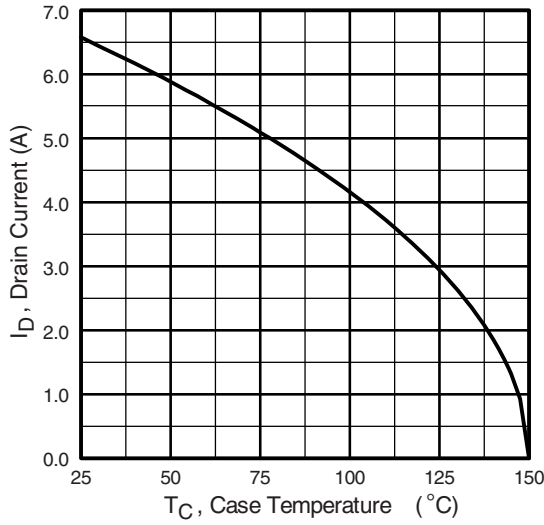


Fig. 9 - Maximum Drain Current vs. Case Temperature

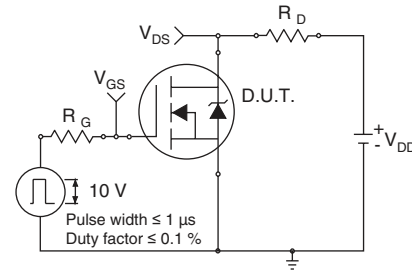


Fig. 10a - Switching Time Test Circuit

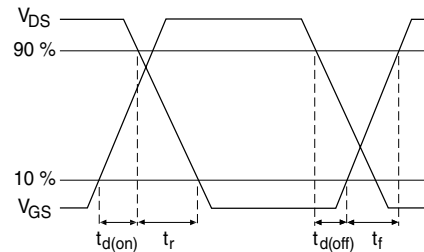


Fig. 10b - Switching Time Waveforms

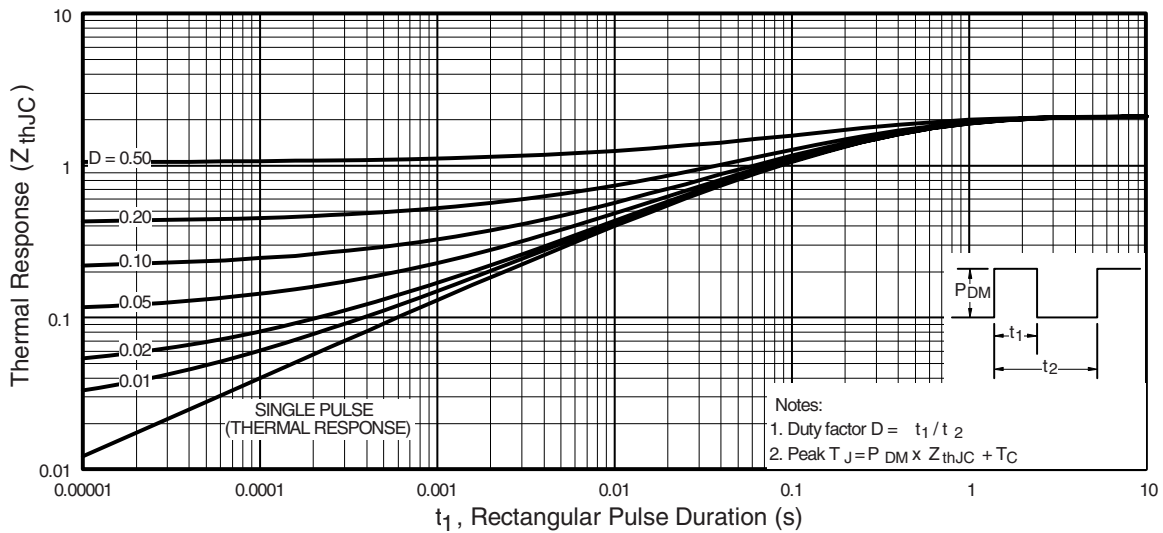


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

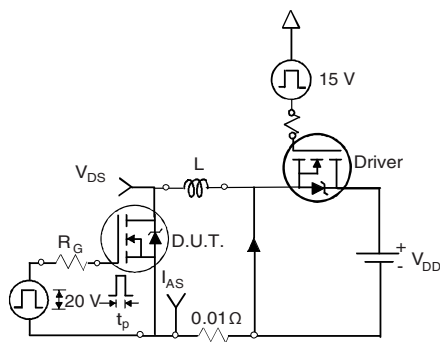


Fig. 12a - Unclamped Inductive Test Circuit

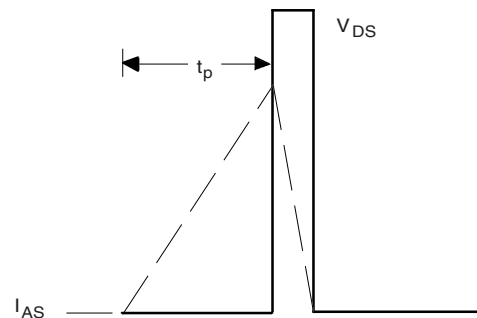


Fig. 12b - Unclamped Inductive Waveforms

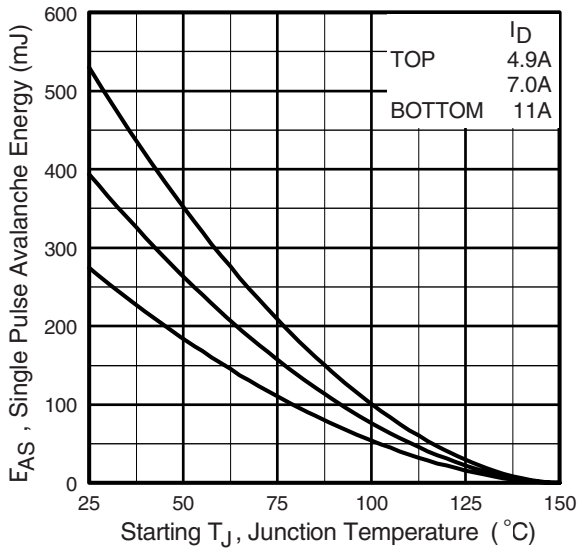


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

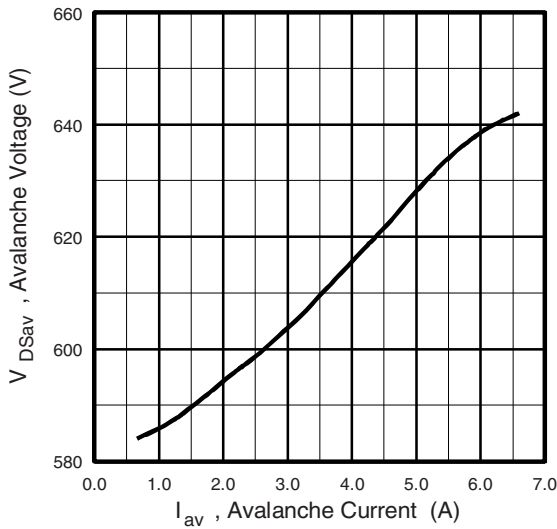


Fig. 12d - Typical Drain-to-Source Voltage vs. Avalanche Current

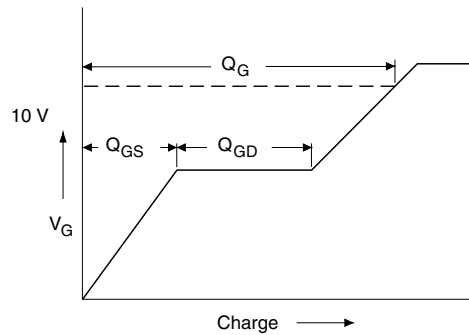


Fig. 13a - Basic Gate Charge Waveform

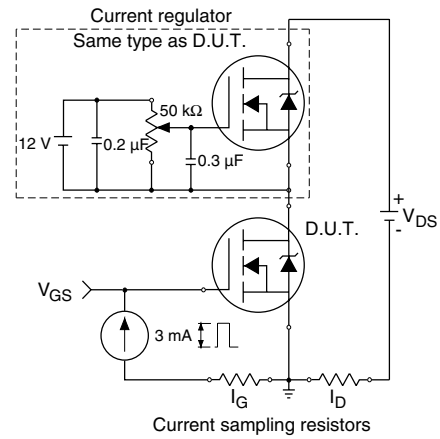
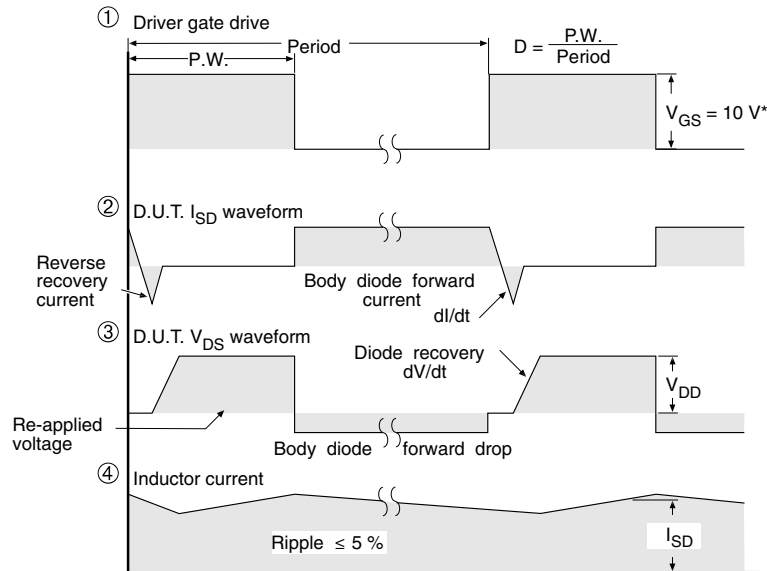
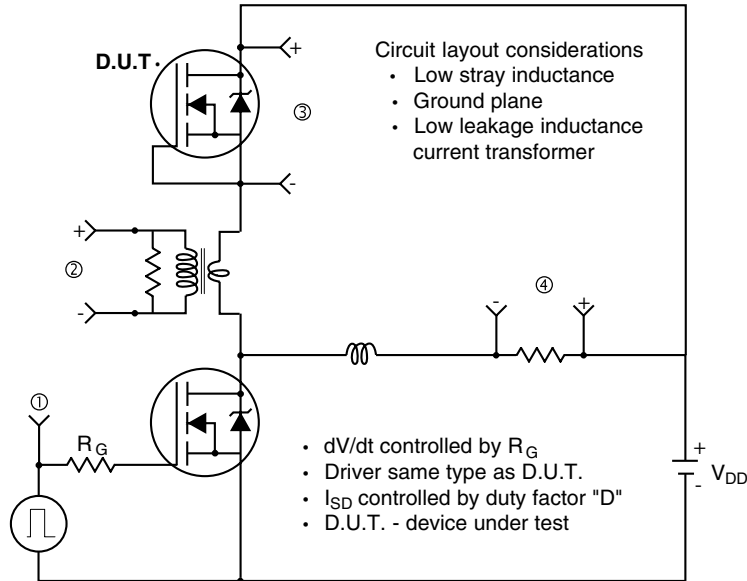


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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